MBR0540T1, MBR0540T3

Surface Mount
Schottky Power Rectifier

SOD−123 Power Surface Mount Package

The Schottky Power Rectifier employs the Schottky Barrier principle with a barrier metal that produces optimal forward voltage drop−reverse current tradeoff. Ideally suited for low voltage, high frequency rectification, or as a free wheeling and polarity protection diodes in surface mount applications where compact size and weight are critical to the system. This package provides an alternative to the leadless 34 MELF style package.

Features

- Guardring for Stress Protection
- Very Low Forward Voltage
- Epoxy Meets UL 94 V−0 @ 0.125 in
- Package Designed for Optimal Automated Board Assembly
- Pb−Free Packages are Available

Mechanical Characteristics

- Reel Options: 3,000 per 7 inch reel/8 mm tape
- Reel Options: 10,000 per 13 inch reel/8 mm tape
- Device Marking: B4
- Polarity Designator: Cathode Band
- Weight: 11.7 mg (approximately)
- Case: Epoxy Molded
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead and Mounting Surface Temperature for Soldering Purposes: 260°C max. for 10 Seconds
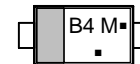
ON Semiconductor®

http://onsemi.com

SCHOTTKY BARRIER
RECTIFIER
0.5 AMPERES, 40 VOLTS

SOD−123
CASE 425
STYLE 1

MARKING DIAGRAM

B4 M■

B4 = Device Code
M = Date Code
■ = Pb−Free Package
(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping[†]
MBR0540T1	SOD−123	3000/Tape & Reel
MBR0540T1G	SOD−123 (Pb−Free)	3000/Tape & Reel
MBR0540T3	SOD−123	10,000/Tape & Reel
MBR0540T3G	SOD−123 (Pb−Free)	10,000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit

Peak Repetitive Reverse Voltage
  Working Peak Reverse Voltage
  DC Blocking Voltage
	V_{RRM}
	V_{RWM}
	V_R
		40	V

Average Rectified Forward Current (At Rated V_R, T_C = 115°C)	I_O	0.5	A
Peak Repetitive Forward Current (At Rated V_R, Square Wave, 20 kHz, T_C = 115°C)	I_{FRM}	1.0	A

Non−Repetitive Peak Surge Current
  (Surge Applied at Rated Load Conditions Halfwave,
  Single Phase, 60 Hz)
	I_{FSM}	5.5	A

Storage/Operating Case Temperature Range	T_{stg}, T_C	−55 to +150	°C
Operating Junction Temperature	T_J	−55 to +150	°C
Voltage Rate of Change (Rated V_R, T_J = 25°C)	dv/dt	1000	V/μs

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Rating	Symbol	Value	Unit
Thermal Resistance – Junction–to–Lead (Note 1) Thermal Resistance – Junction–to–Ambient (Note 2)	R_{tjl} R_{tja}	118 206	°C/W

ELECTRICAL CHARACTERISTICS

		T_J = 25°C	T_J = 100°C	
Maximum Instantaneous Forward Voltage (Note 3)	v_F			V
(i_F = 0.5 A) (i_F = 1 A)		0.51 0.62	0.46 0.61	
		T_J = 25°C	T_J = 100°C	
Maximum Instantaneous Reverse Current (Note 3)	I_R			μA
(V_R = 40 V) (V_R = 20 V)		20 10	13,000 5,000	

1. Mounted with minimum recommended pad size, PC Board FR4.
2. 1 inch square pad size (1 X 0.5 inch for each lead) on FR4 board.
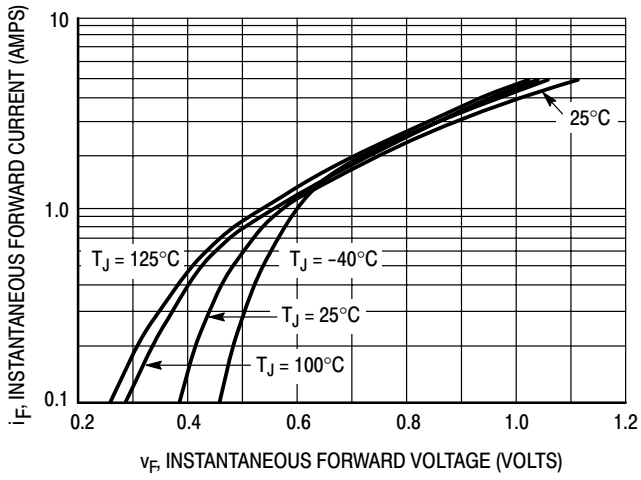3. Pulse Test: Pulse Width ≤ 250 μs, Duty Cycle ≤ 2.0%.

Figure 1. Typical Forward Voltage

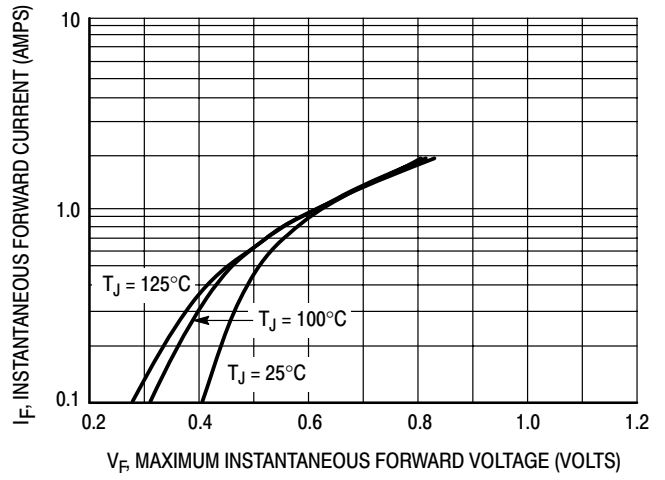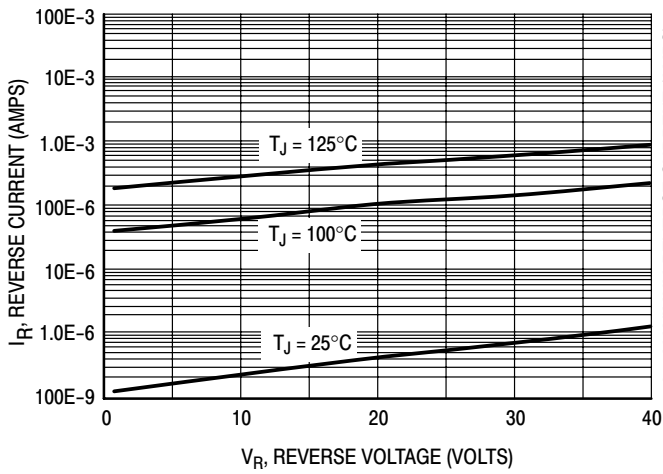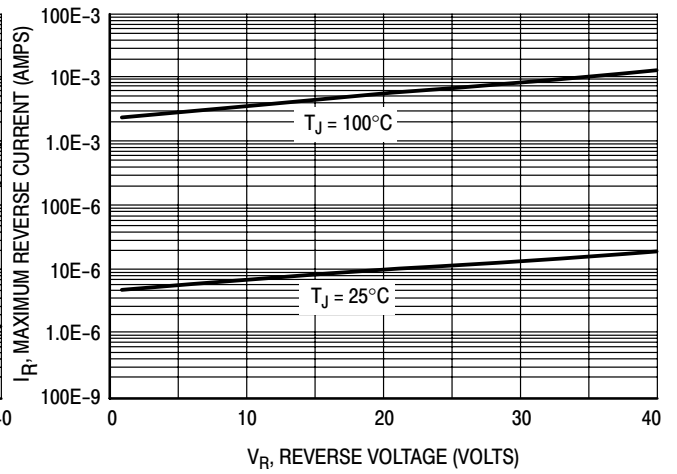**Figure 2. Maximum Forward Voltage**

Figure 3. Typical Reverse Current
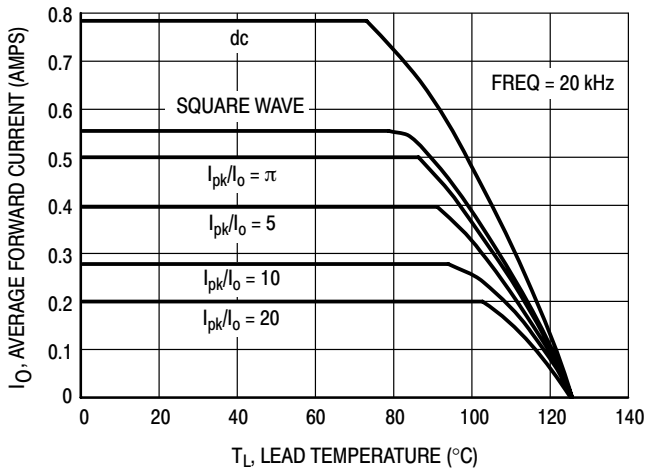

Figure 4. Maximum Reverse Current

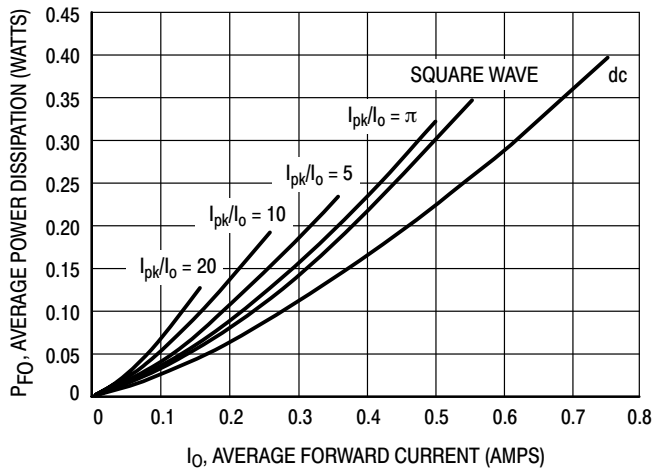**Figure 5. Current Derating**

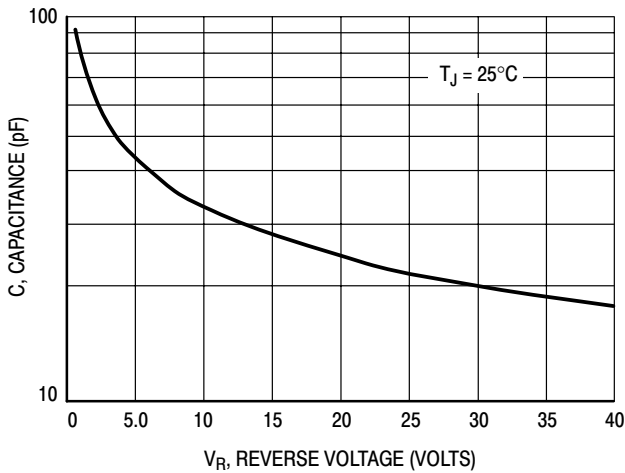**Figure 6. Forward Power Dissipation**
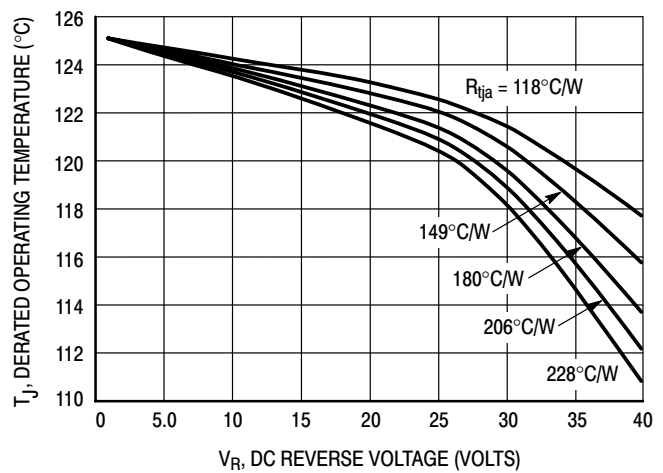
Figure 7. Capacitance

Figure 8. Typical Operating Temperature Derating*

* Reverse power dissipation and the possibility of thermal runaway must be considered when operating this device under any reverse voltage conditions. Calculations of T_J therefore must include forward and reverse power effects. The allowable operating T_J may be calculated from the equation: $T_J = T_{Jmax} - r(t)(Pf + Pr)$ where
    r(t) = thermal impedance under given conditions,
    Pf = forward power dissipation, and
    Pr = reverse power dissipation
This graph displays the derated allowable T_J due to reverse bias under DC conditions only and is calculated as $T_J = T_{Jmax} - r(t)Pr$, where r(t) = Rthja. For other power applications further calculations must be performed.
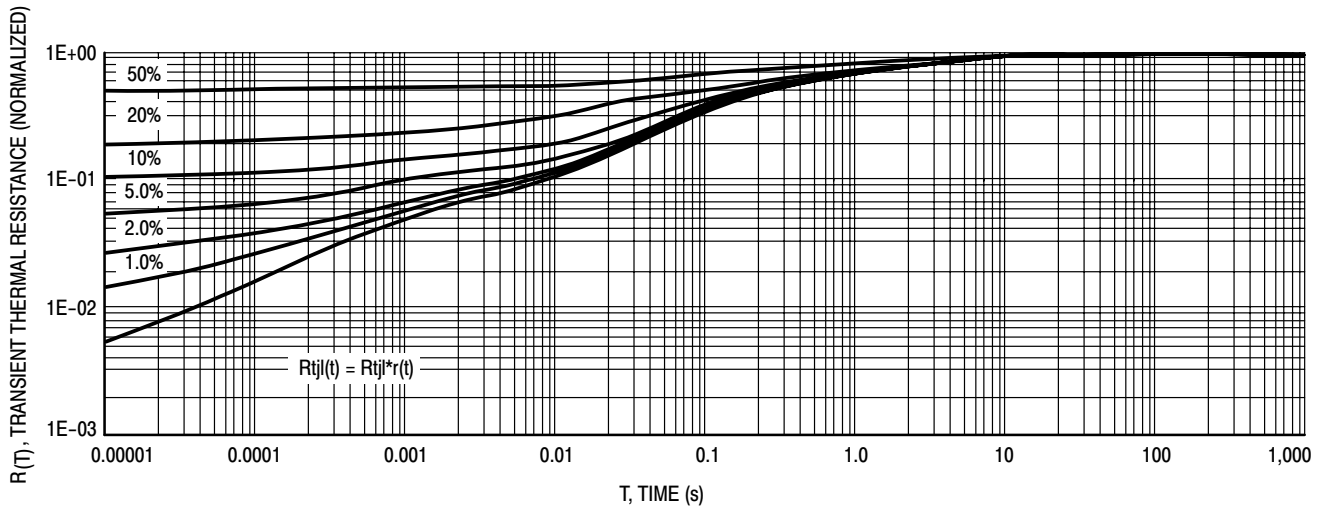
Figure 9. Thermal Response Junction to Lead
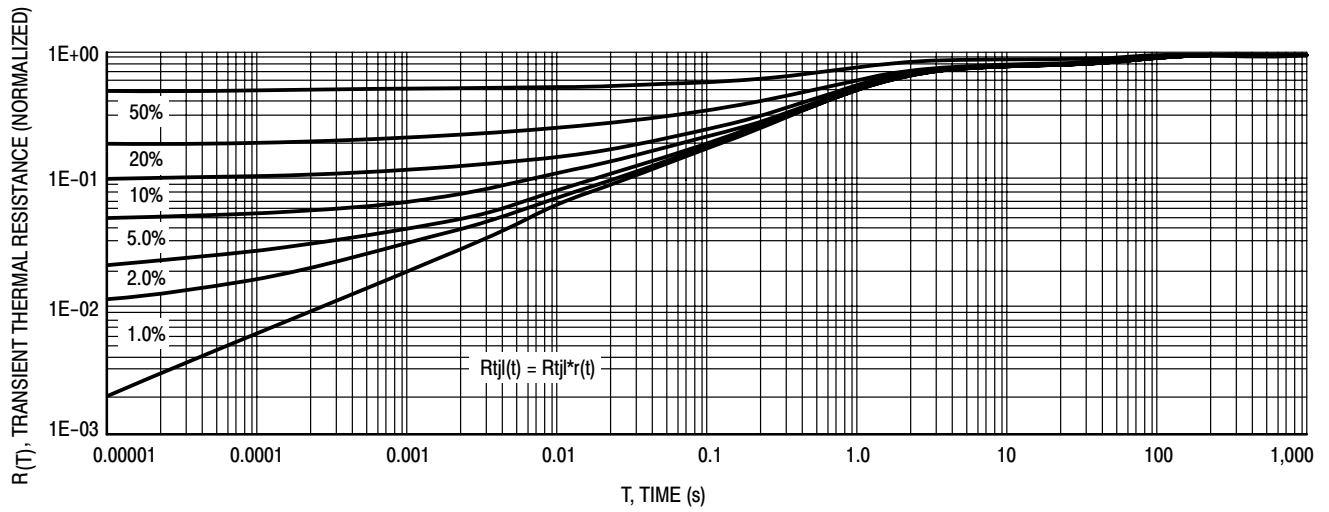
Figure 10. Thermal Response Junction to Ambient
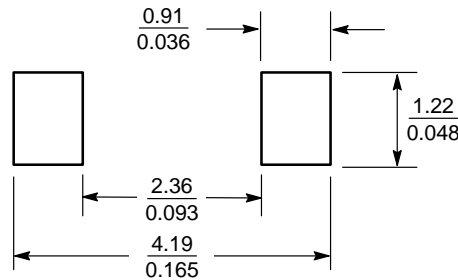
PACKAGE DIMENSIONS

SOD–123
PLASTIC
CASE 425–04
ISSUE C
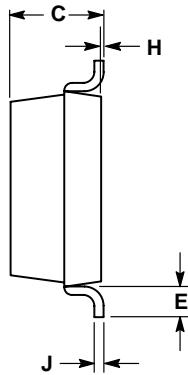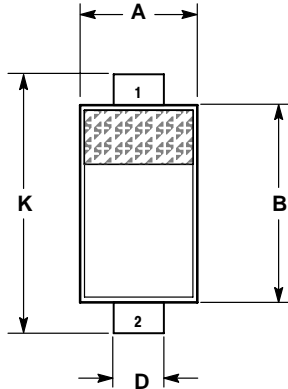
NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.055	0.071	1.40	1.80
B	0.100	0.112	2.55	2.85
C	0.037	0.053	0.95	1.35
D	0.020	0.028	0.50	0.70
E	0.004	---	0.25	---
H	0.000	0.004	0.00	0.10
J	---	0.006	---	0.15
K	0.140	0.152	3.55	3.85

STYLE 1:
PIN 1. CATHODE
     2. ANODE

SOLDERING FOOTPRINT*

SCALE 10:1 $\left(\dfrac{mm}{inches}\right)$

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.